

(19) **United States**

(12) **Patent Application Publication**

KIMURA

(10) **Pub. No.: US 2024/0213258 A1**

(43) **Pub. Date: Jun. 27, 2024**

(54) **SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME**

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(21) Appl. No.: **18/435,283**

(22) Filed: **Feb. 7, 2024**

Related U.S. Application Data

(63) Continuation of application No. 17/586,947, filed on Jan. 28, 2022, now Pat. No. 11,942,483, which is a continuation of application No. 16/120,657, filed on Sep. 4, 2018, now abandoned, which is a continuation of application No. 15/467,231, filed on Mar. 23, 2017, now Pat. No. 10,068,926, which is a continuation of application No. 15/360,226, filed on Nov. 23, 2016, now Pat. No. 10,283,530, which is a continuation of application No. 14/718,333, filed on May 21, 2015, now Pat. No. 9,508,862, which is a continuation of application No. 14/221,753, filed on Mar. 21, 2014, now Pat. No. 9,040,995, which is a continuation of application No. 13/462,945, filed on May 3, 2012, now Pat. No. 8,680,529.

Foreign Application Priority Data

May 5, 2011 (JP) 2011-103344

Publication Classification

(51) **Int. Cl.**
H01L 27/12 (2006.01)
H01L 29/04 (2006.01)
H01L 29/786 (2006.01)
H10K 59/121 (2006.01)
H10K 59/123 (2006.01)

(52) **U.S. Cl.**
CPC *H01L 27/1225* (2013.01); *H01L 27/1248* (2013.01); *H01L 29/045* (2013.01); *H01L 29/786* (2013.01); *H01L 29/78648* (2013.01); *H01L 29/7869* (2013.01); *H01L 27/1259* (2013.01); *H01L 27/1262* (2013.01); *H10K 59/1213* (2023.02); *H10K 59/123* (2023.02)

ABSTRACT

A semiconductor device includes a pixel electrode and a transistor which includes a first gate electrode, a first insulating layer over the first gate electrode, a semiconductor layer over the first insulating layer, a second insulating layer over the semiconductor layer, and a second gate electrode. The pixel electrode and the second gate electrode are provided over the second insulating layer. The first gate electrode has a region overlapping with the semiconductor layer with the first insulating layer provided therebetween. The second gate electrode has a region overlapping with the semiconductor layer with the second insulating layer provided therebetween. A first region is at least part of a region where the second gate electrode overlaps with the semiconductor layer. A second region is at least part of a region where the pixel electrode is provided. The second insulating layer is thinner in the first region than in the second region.

